P-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

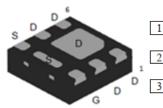
- Load Switches
- DC/DC Conversion
- Motor Drives

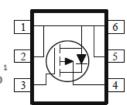
PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
-30	$30 @ V_{GS} = -4.5V$	-8.2	
	42 @ V _{GS} = -2.5V	-7.0	





FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			-30	V		
Gate-Source Voltage		V_{GS}	±12	V		
Continuous Drain Current®	T _A =25°C		-8.2			
Continuous Drain Current ^a	T _A =70°C	l _D	-6.5	Α		
Pulsed Drain Current ^b		I _{DM}	-30	'		
Continuous Source Current (Diode Conduction) a		I _S	-3	Α		
Down Dissipation a	T _A =25°C T _A =70°C	- P _D	3	W		
Power Dissipation ^a	T _A =70°C] ' [*] D	1.9	v V		
Operating Junction and Storage Temperature Range		T_J, T_{sta}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Ambient	Steady State	IN _θ JΑ	90	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

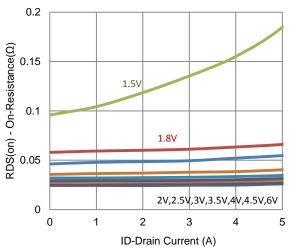
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-12			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$			30	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -1.6 \text{ A}$			42	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A}$		6		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.73		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		29			
Gate-Source Charge	Q_{gs}	$I_{D} = -2 \text{ A}$		3.9		nC	
Gate-Drain Charge	Q_gd	10 - 2 A		7.1			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -15 \text{ V}, R_1 = 7.5 \Omega,$		15			
Rise Time	t _r	$V_{DS} = -15 \text{ V}, K_L - 7.5 \Omega,$ $I_D = -2 \text{ A},$		20		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		81		ns	
Fall Time	t _f	VGEN = 4.5 V, NGEN = 0.32		37			
Input Capacitance	C _{iss}			1483			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		134		pF	
Reverse Transfer Capacitance	C_{rss}			114			

Notes

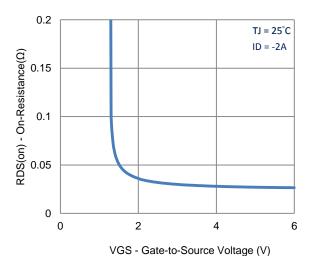
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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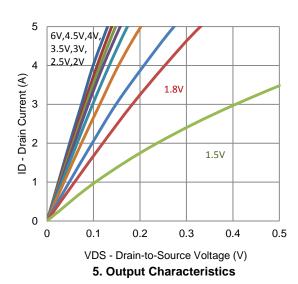
Typical Electrical Characteristics



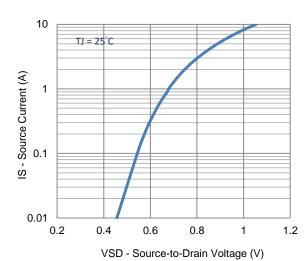
1. On-Resistance vs. Drain Current



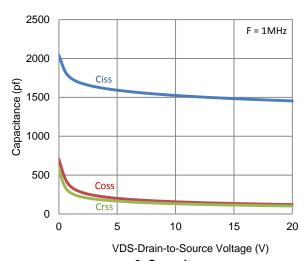
3. On-Resistance vs. Gate-to-Source Voltage



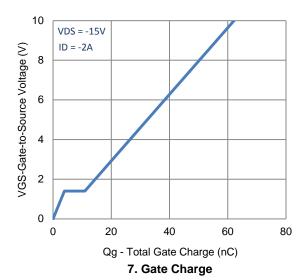
2. Transfer Characteristics

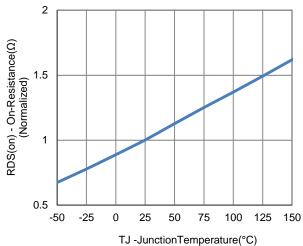


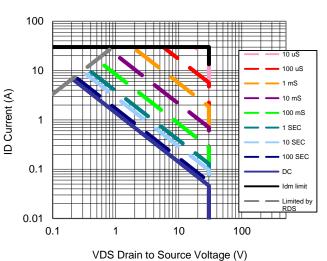
4. Drain-to-Source Forward Voltage

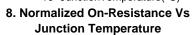


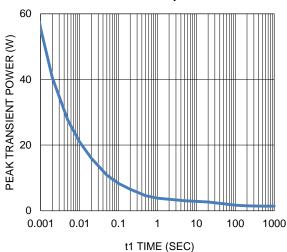
Typical Electrical Characteristics





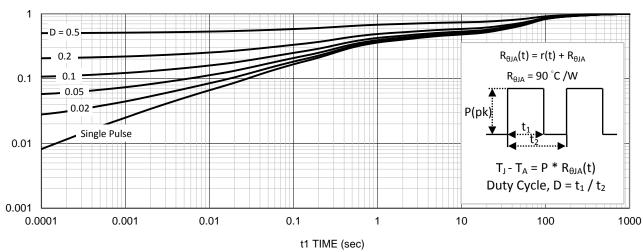






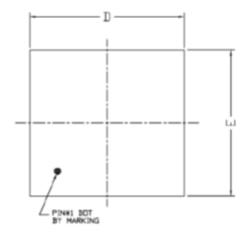
9. Safe Operating Area

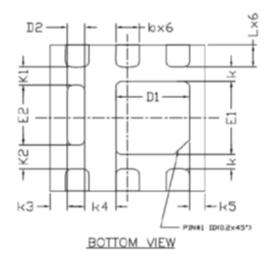
10. Single Pulse Maximum Power Dissipation

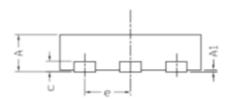


11. Normalized Thermal Transient Junction to Ambient

Package Information







	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0, 50	0, 55	0.60	0, 020	0.022	0.024	
A1	0.00		0.05	0.000		0.002	
ъ	0.25	0.30	0.35	0.010	0.012	0.014	
С		0.152 REF			0.006 REF		
D	1.90	2.00	2. 10	0.075	0.079	0.083	
D1	0.85	0.95	1.05	0.033	0.037	0.041	
D2	0.13	0.23	0.33	0.005	0.009	0.013	
E	1.90	2.00	2.10	0.075	0.079	0.083	
E1	0.90	1.00	1.10	0.035	0.039	0.043	
E2	0.72	0.82	0.92	0.028	0.032	0.036	
c	0.65 BSC			0.026 BSC			
K	0, 20 BSC		0.008 BSC				
K1	0, 25 BSC			0.010 BSC			
K2	0. 33 BSC			0.013 BSC			
K3	0. 22 BSC			0.009 BSC			
K4	0.40 BSC			0.016 BSC			
K5		0.20 BSC			0.008 BSC		
L	0, 25	0.30	0.35	0,010	0,012	0.014	